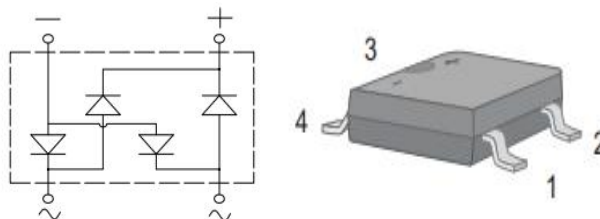


### Bridge Rectifier Diode 整流桥

#### ■ Features 特点

Glass passivated chip junction 玻璃钝化结  
High surge current capability 高浪涌电流能力  
Reflow Solder Temperature 220°C 回流焊温度 220 度  
Package 封装: MBF



#### ■ Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	MB1F	MB2F	MB4F	MB6F	MB8F	MB10F	Unit 单位
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	$I_F$	0.8						A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	30						A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	90						$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	150 $^{\circ}\text{C}$ , -55to+150 $^{\circ}\text{C}$						

#### ■ Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压降	$V_F$		1.1		V	$I_F=0.8\text{A}$
Reverse Current ( $T_A=25^{\circ}\text{C}$ ) 反向漏电流( $T_A=125^{\circ}\text{C}$ )	$I_R$			5 40	$\mu\text{A}$	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_D$		13		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

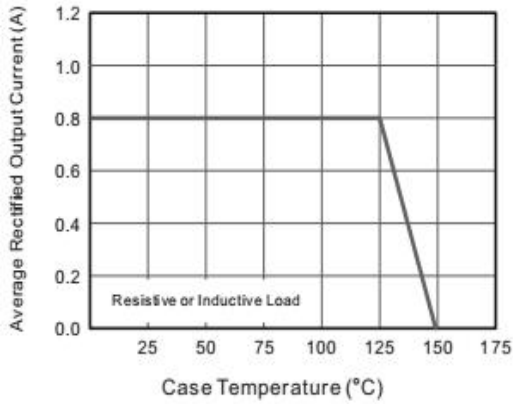


Figure 1: Forward Current Derating Curve

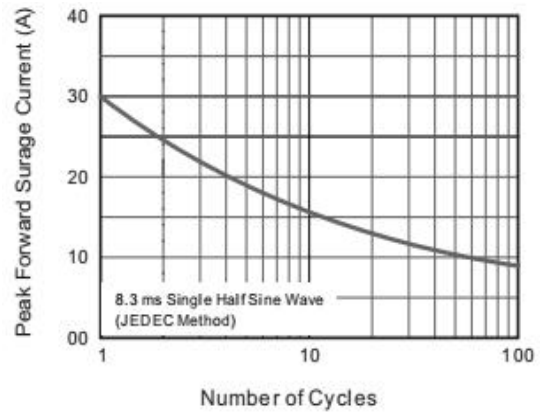


Figure 2: Peak Forward Surge Current

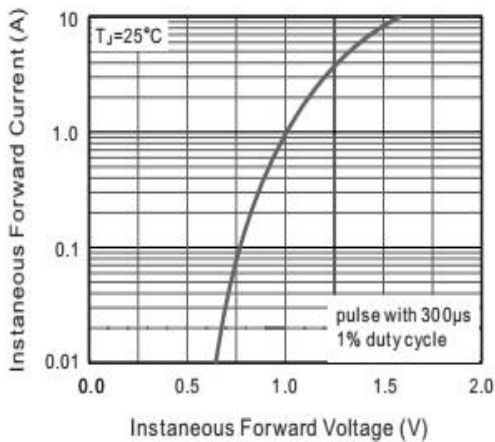


Figure 3: Instantaneous Forward Characteristics

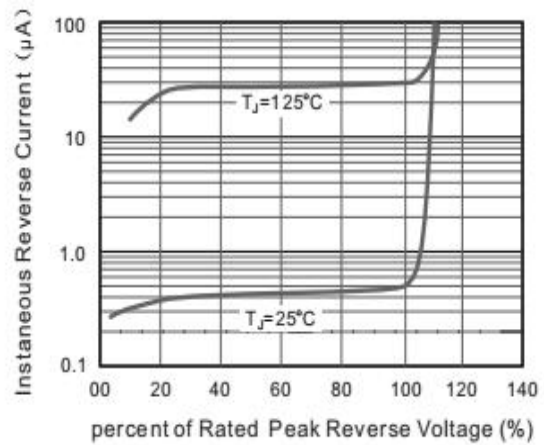


Figure 4: Reverse Leakage Characteristics

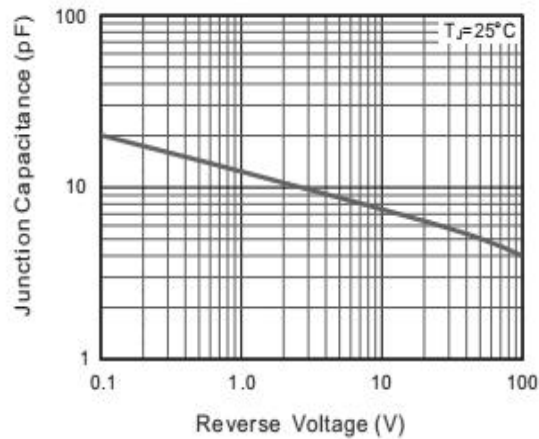
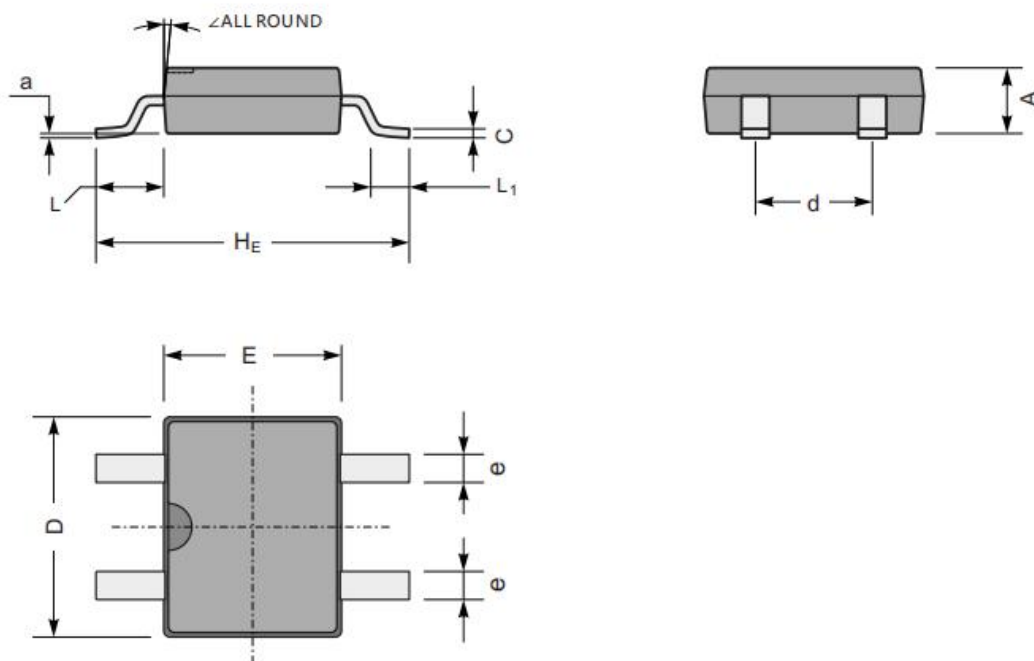


Figure 5: Junction Capacitance Characteristics

■Dimension 外形封装尺寸



MBF mechanical data

UNIT		A	C	D	E	HE	d	e	L	L <sub>1</sub>	a	∠
mm	max	1.6	0.22	5.0	4.1	7.0	2.7	0.8	1.7	1.1	0.2	7°
	min	1.2	0.15	4.5	3.6	6.4	2.3	0.5	1.3	0.5	—	
mil	max	63	8.7	197	161	276	106	31	67	43	8	
	min	47	5.9	177	142	252	91	20	51	20	—	